

CD4070BM/CD4070BC **Quad 2-Input EXCLUSIVE-OR Gate** **CD4077BM/CD4077BC** **Quad 2-Input EXCLUSIVE-NOR Gate**

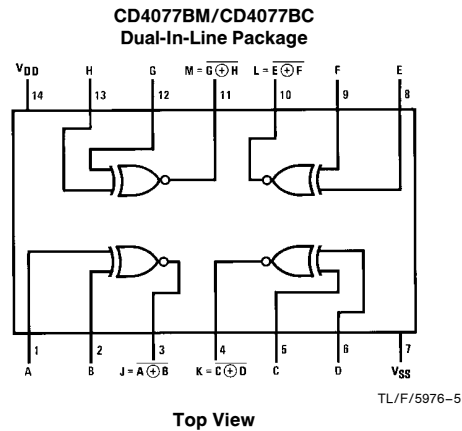
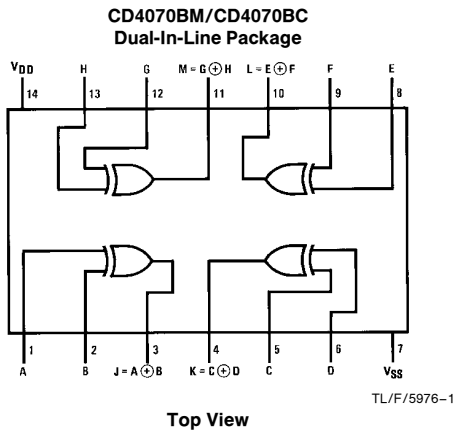
General Description

Employing complementary MOS (CMOS) transistors to achieve wide power supply operating range, low power consumption, and high noise margin, the CD4070BM/BC and CD4077BM/BC provide basic functions used in the implementation of digital integrated circuit systems. The N- and P-channel enhancement mode transistors provide a symmetrical circuit with output swing essentially equal to the supply voltage. No DC power other than that caused by leakage current is consumed during static condition. All inputs are protected from damage due to static discharge by diode clamps to V_{DD} and V_{SS} .

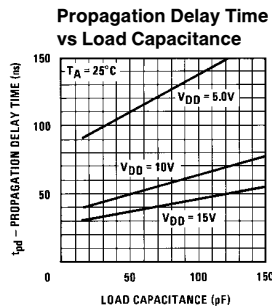
Features

- Wide supply voltage range 3.0V to 15V
- High noise immunity 0.45 V_{DD} typ.
- Low power TTL compatibility Fan out of 2 driving 74L or 1 driving 74LS
- CD4070B—Pin compatible to CD4030A
—Equivalent to MM54C86/MM74C86 and MC14070B
- CD4077B—Equivalent to MC14077B

Connection Diagram



Typical Performance Characteristics



Truth Tables

CD4070BM/CD4070BC			CD4077BM/CD4077BC		
Inputs		Outputs	Inputs		Outputs
A	B	Y	A	B	Y
L	L	L	L	L	H
L	H	H	L	H	L
H	L	H	H	L	L
H	H	L	H	H	H

Absolute Maximum Ratings (Notes 1 and 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

DC Supply Voltage (V_{DD})	−0.5 to +18 V_{DC}
Input Voltage (V_{IN})	−0.5 to V_{DD} + 0.5 V_{DC}
Storage Temperature Range (T_S)	−65°C to +150°C
Power Dissipation (P_D)	
Dual-In-Line	700 mW
Small Outline	500 mW
Lead Temperature (T_L)	
(Soldering, 10 seconds)	260°C

Recommended Operating Conditions (Note 2)

DC Supply Voltage (V_{DD})	3V to 15 V_{DC}
Input Voltage (V_{IN})	0 to V_{DD} V_{DC}
Operating Temperature Range (T_A)	
CD4070BC/CD4077BC	−40°C to +85°C
CD4070BM/CD4077BM	−55°C to +125°C

DC Electrical Characteristics CD4070BM/CD4077BM (Note 2)

Symbol	Parameter	Conditions	−55°C		+25°C			+125°C		Units
			Min	Max	Min	Typ	Max	Min	Max	
I_{DD}	Quiescent Device Current	$V_{DD} = 5V$, $V_{IN} = V_{DD}$ or V_{SS}		0.25			0.25		7.5	μA
		$V_{DD} = 10V$, $V_{IN} = V_{DD}$ or V_{SS}		0.5			0.5		15	μA
		$V_{DD} = 15V$, $V_{IN} = V_{DD}$ or V_{SS}		1.0			1.0		30	μA
V_{OL}	Low Level Output Voltage	$ I_O < 1 \mu A$								
		$V_{DD} = 5V$		0.05		0	0.05		0.05	V
		$V_{DD} = 10V$		0.05		0	0.05		0.05	V
		$V_{DD} = 15V$		0.05		0	0.05		0.05	V
V_{OH}	High Level Output Voltage	$ I_O < 1 \mu A$								
		$V_{DD} = 5V$	4.95		4.95	5		4.95		V
		$V_{DD} = 10V$	9.95		9.95	10		9.95		V
		$V_{DD} = 15V$	14.95		14.95	15		14.95		V
V_{IL}	Low Level Input Voltage	$ I_O < 1 \mu A$								
		$V_{DD} = 5V$, $V_O = 4.5V$ or $0.5V$		1.5			1.5		1.5	V
		$V_{DD} = 10V$, $V_O = 9V$ or $1.0V$		3.0			3.0		3.0	V
		$V_{DD} = 15V$, $V_O = 13.5V$ or $1.5V$		4.0			4.0		4.0	V
V_{IH}	High Level Input Voltage	$ I_O < 1 \mu A$								
		$V_{DD} = 5V$, $V_O = 0.5V$ or $4.5V$	3.5		3.5			3.5		V
		$V_{DD} = 10V$, $V_O = 1.0V$ or $9.0V$	7.0		7.0			7.0		V
		$V_{DD} = 15V$, $V_O = 1.5V$ or $13.5V$	11.0		11.0			11.0		V
I_{OL}	Low Level Output Current (Note 3)	$V_{DD} = 5V$, $V_O = 0.4V$	0.64		0.51	0.88		0.36		mA
		$V_{DD} = 10V$, $V_O = 0.5V$	1.6		1.3	2.25		0.9		mA
		$V_{DD} = 15V$, $V_O = 1.5V$	4.2		3.4	8.8		2.4		mA
I_{OH}	High Level Output Current (Note 3)	$V_{DD} = 5V$, $V_O = 4.6V$	−0.64		−0.51	−0.88		−0.36		mA
		$V_{DD} = 10V$, $V_O = 9.5V$	−1.6		−1.3	−2.25		−0.9		mA
		$V_{DD} = 15V$, $V_O = 13.5V$	−4.2		−3.4	−8.8		−2.4		mA
I_{IN}	Input Current	$V_{DD} = 15V$, $V_{IN} = 0V$		−0.1		-10^{-5}	−0.1		−1.0	μA
		$V_{DD} = 15V$, $V_{IN} = 15V$		0.1		10^{-5}	0.1		1.0	μA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation.

Note 2: $V_{SS} = 0V$ unless otherwise specified.

Note 3: I_{OL} and I_{OH} are tested one output at a time.

DC Electrical Characteristics CD4070BC/CD4077BC (Note 2)

Symbol	Parameter	Conditions	− 40°C		+ 25°C			+ 85°C		Units
			Min	Max	Min	Typ	Max	Min	Max	
I _{DD}	Quiescent Device Current	V _{DD} = 5V, V _{IN} = V _{DD} or V _{SS}		1.0			1.0		7.5	μA
		V _{DD} = 10V, V _{IN} = V _{DD} or V _{SS}		2.0			2.0		15	μA
		V _{DD} = 15V, V _{IN} = V _{DD} or V _{SS}		4.0			4.0		30	μA
V _{OL}	Low Level Output Voltage	I _O < 1 μA								
		V _{DD} = 5V		0.05		0	0.05		0.05	V
		V _{DD} = 10V		0.05		0	0.05		0.05	V
		V _{DD} = 15V		0.05		0	0.05		0.05	V
V _{OH}	High Level Output Voltage	I _O < 1 μA								
		V _{DD} = 5V	4.95		4.95	5		4.95		V
		V _{DD} = 10V	9.95		9.95	10		9.95		V
		V _{DD} = 15V	14.95		14.95	15		14.95		V
V _{IL}	Low Level Input Voltage	I _O < 1 μA								
		V _{DD} = 5V, V _O = 4.5V or 0.5V		1.5			1.5		1.5	V
		V _{DD} = 10V, V _O = 9V or 1.0V		3.0			3.0		3.0	V
		V _{DD} = 15V, V _O = 13.5V or 1.5V		4.0			4.0		4.0	V
V _{IH}	High Level Input Voltage	I _O < 1 μA								
		V _{DD} = 5V, V _O = 0.5V or 4.5V	3.5		3.5			3.5		V
		V _{DD} = 10V, V _O = 1V or 9.0V	7.0		7.0			7.0		V
		V _{DD} = 15V, V _O = 1.5V or 13.5V	11.0		11.0			11.0		V
I _{OL}	Low Level Output Current	V _{DD} = 5V, V _O = 0.4V	0.52		0.44	0.88		0.36		mA
		V _{DD} = 10V, V _O = 0.5V	1.3		1.1	2.25		0.9		mA
		V _{DD} = 15V, V _O = 1.5V	3.6		3.0	8.8		2.4		mA
I _{OH}	High Level Output Current	V _{DD} = 5V, V _O = 4.6V	−0.52		−0.44	−0.88		−0.36		mA
		V _{DD} = 10V, V _O = 9.5V	−1.3		−1.1	−2.25		−0.9		mA
		V _{DD} = 15V, V _O = 13.5V	−3.6		−3.0	−8.8		−2.4		mA
I _{IN}	Input Current	V _{DD} = 15V, V _{IN} = 0V		−0.3		−10 ^{−5}	−0.3		−1.0	μA
		V _{DD} = 15V, V _{IN} = 15V		0.3		10 ^{−5}	0.3		1.0	μA

AC Electrical Characteristics*

T_A = 25°C, C_L = 50 pF, R_L = 200k, t_r and t_f ≤ 20 ns, unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t _{PHL} or t _{PLH}	Propagation Delay Time from Input to Output	V _{DD} = 5V		110	185	ns
		V _{DD} = 10V		50	90	ns
		V _{DD} = 15V		40	75	ns
t _{THL} or t _{TLH}	Transition Time	V _{DD} = 5V		100	200	ns
		V _{DD} = 10V		50	100	ns
		V _{DD} = 15V		40	80	ns
C _{IN}	Average Input Capacitance	Any Input		5	7.5	pF
C _{PD}	Power Dissipation Capacitance	Any Input (Note 4)		20		pF

*AC Parameters are guaranteed by DC correlated testing.

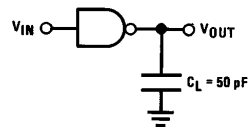
Note 1: “Absolute Maximum Ratings” are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of “Recommended Operating Conditions” and “Electrical Characteristics” provides conditions for actual device operation.

Note 2: V_{SS} = 0V unless otherwise specified.

Note 3: I_{OL} and I_{OH} are tested one output at a time.

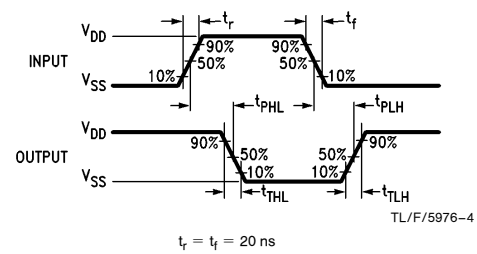
Note 4: C_{PD} determines the no load AC power consumption of any CMOS device. For complete explanation, see 54C/74C Family Characteristics Application Note—AN-90.

AC Test Circuit and Switching Time Waveforms

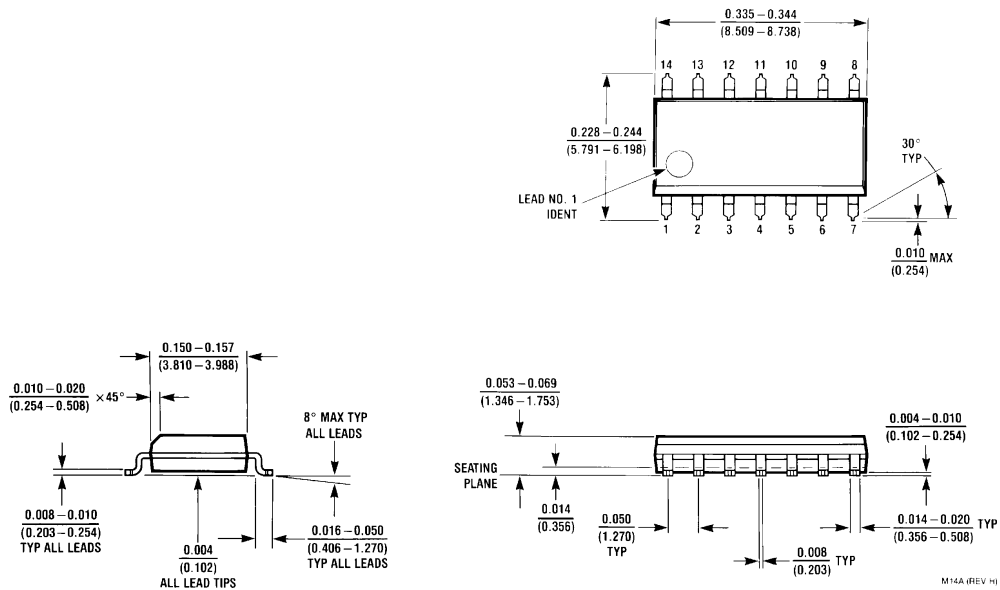


Note: Delays measured with input $t_r, t_f = 20 \text{ ns}$.

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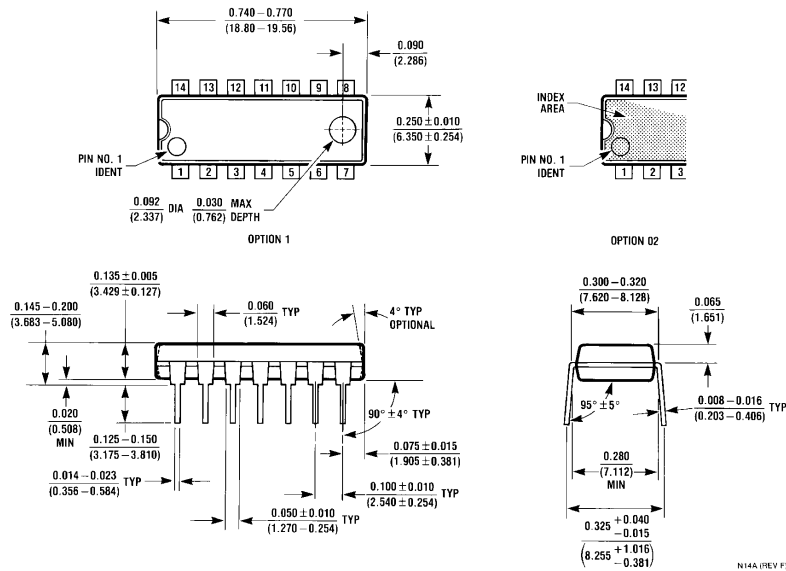


Physical Dimensions inches (millimeters)



Molded Small Outline Package (M)
Order Number CD4070BCM or CD4077BCM
NS Package Number M14A

M14A (REV H)

Physical Dimensions inches (millimeters) (Continued)**LIFE SUPPORT POLICY**

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